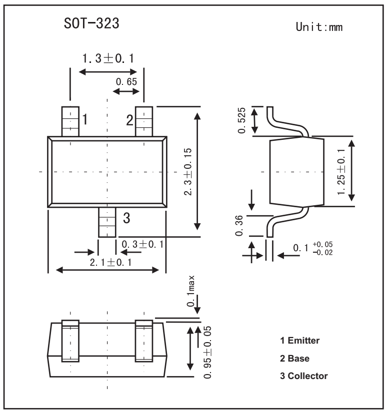
Silicon NPN Epitaxial Planar Type

2SC4562



■ Features

- ● High transition frequency f_T.
- ● Small collector output capacitance cob.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base voltage	V_{CBO}	I_C = 10 μA, I_E = 0	50			V
Collector-emitter voltage	V_{CEO}	I_C = 1 mA, I_B = 0	50			V
Emitter-base voltage	V_{EBO}	I_E = 10 μA, I_C = 0	5			V
Collector cutoff current	I_{CBO}	V_{CB} = 10 V, I_E = 0			0.1	μA
Emitter cutoff current	I_{EBO}	V_{CE} = 10 V, I_B = 0			100	μA
Forward current transfer ratio	h_{FE}	V_{CE} = 10 V, I_C = 2 mA	200		500	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = 10 mA, I_B = 1 mA		0.06	0.30	V
Transition frequency	f_T	V_{CB} = 10 V, I_E = -2 mA, f = 200 MHz		250		MHz
Collector output capacitance	C_{ob}	V_{CB} = 10 V, I_E = 0, f = 1 MHz		1.5		pF

■ h_{FE} Classification

Marking	AM	
Rank	Q	R
h_{FE}	200～400	250～500